

## 2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

## Future Normal in Semiconductor

2025-02-13(목), 10:55-12:40 좌장: 추후업데이트 예정

## K. Memory (Design & Process Technology) 분과

## [TK2-K] Embedded Memory and Computing-in-Memory Application

초청 TK2-K-1 10:55-11:25	State-of-the-Art of High-density Cross-point STT-MRAM Technology Soo Man Seo, Soo Gil Kim, and, Jae Yun Yi, and Seon Yong Cha RnD division, SK hynix Inc.
ТК2-К-2 11:25-11:40	Embedded RRAM Technology: an Extremely Cost-Effective eNVM Solution with Full CMOS Logic CompatibilitySooan Kim, Jaehun Lee, Nayan Chandra Das, Yongseok Chung, Sungchan Lim, Hwanho Ma, Youngdong Kim, Daeyun Kang, Kyongsik Yeom, Changmin Jeon, and Kangho Lee Foundry Business, Samsung Electronics Co.
ТК2-К-3 11:40-11:55	Revealing the Switching Mechanism of ECRAM through an Independently-Contacted WOx Double Layer Seungmin Han, Hyunjeong Kwak, Jinho Byun, Jeonghoon Son, Seungkun Kim, and Seyoung Kim Dept. of Materials Science and Engineering, POSTECH
TK2-K-4 11:55-12:10	In-memory Parallel Computing with Variation Tolerant Memristive Majority Logic in a Crossbar Array. Moon Gu Choi and Kyung Min Kim Department of Materials Science and Engineering, KAIST
TK2-K-5 12:10-12:25	Experimental Implementation of Programmable Threshold Logic in a Memristor Crossbar Array Sangwook Youn, Jinwoo Park, and Hyungjin Ki <sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University
ТК2-К-6 12:25-12:40	Demonstration of Convolution Kernel Operation Using Memristor Crossbar Array with Quantized Weights and Binary Activation Jinwoo Park, Sangwook Youn, and Hyungjin Kim <sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University